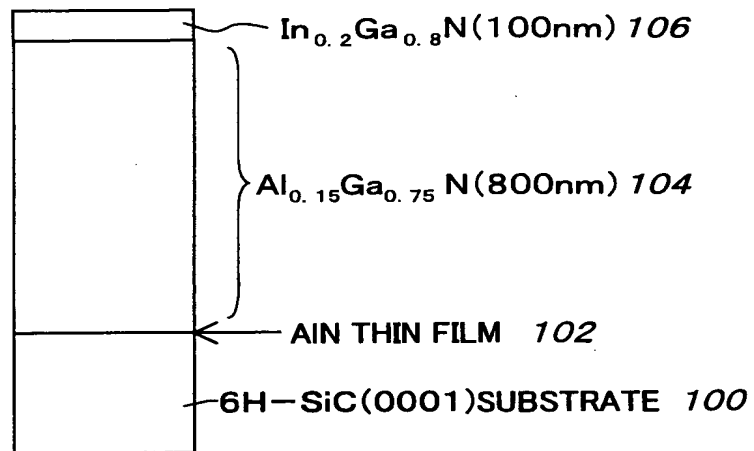


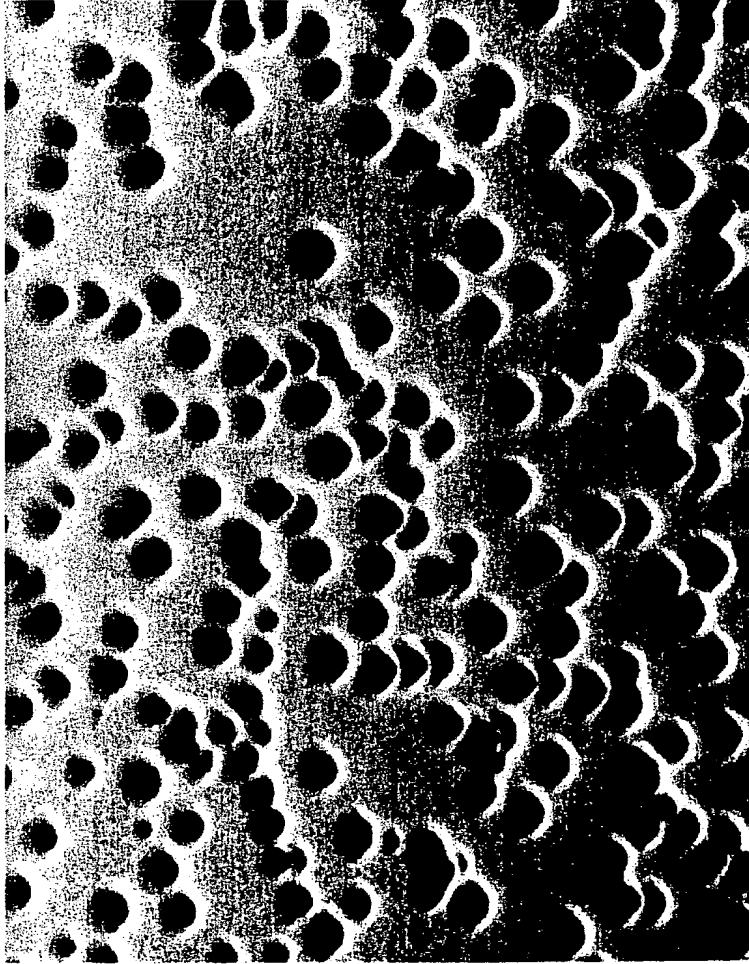
FIG. 1



094322 03101
T0E80" 222E4660

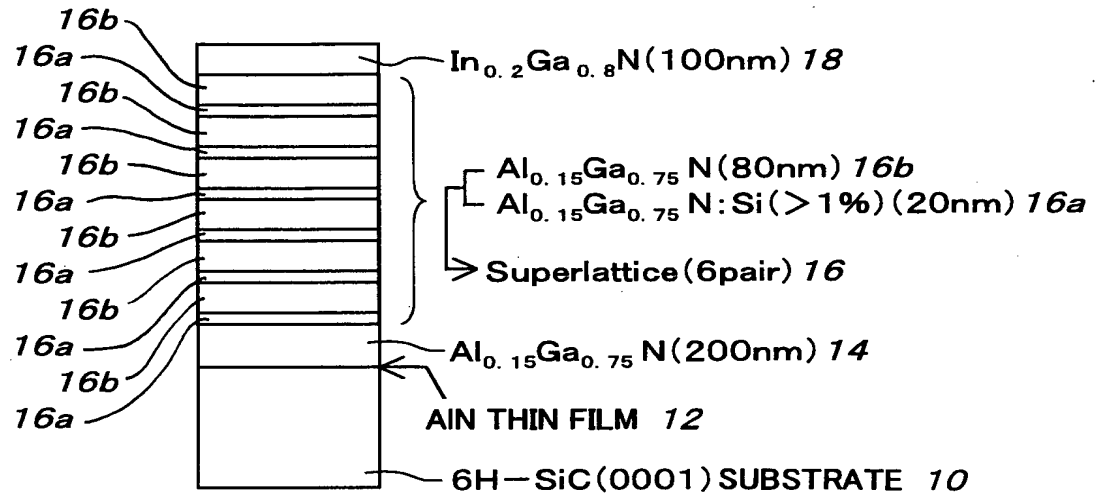
FOIEBO" 222E4660

FIG. 2



0.5 μm

FIG. 3



101E90" 222E4650

FIG. 4

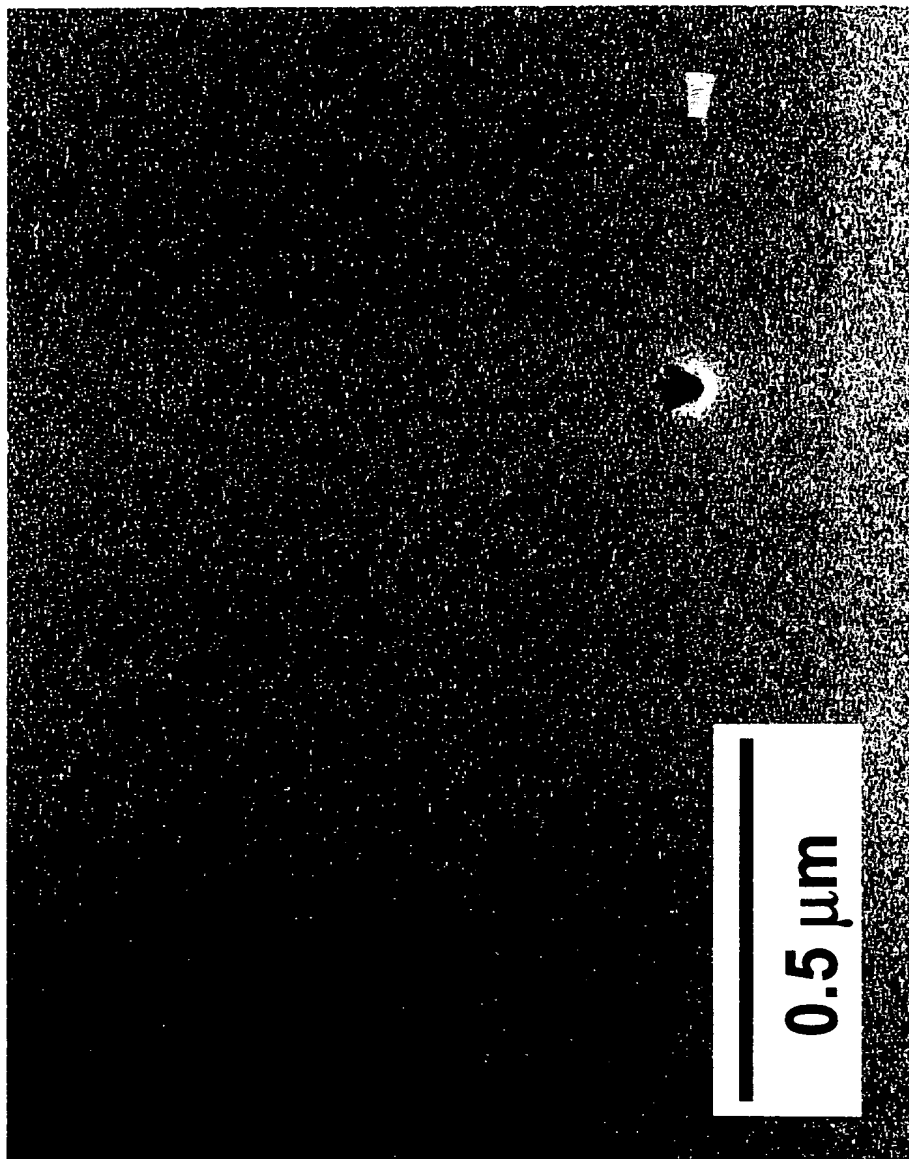
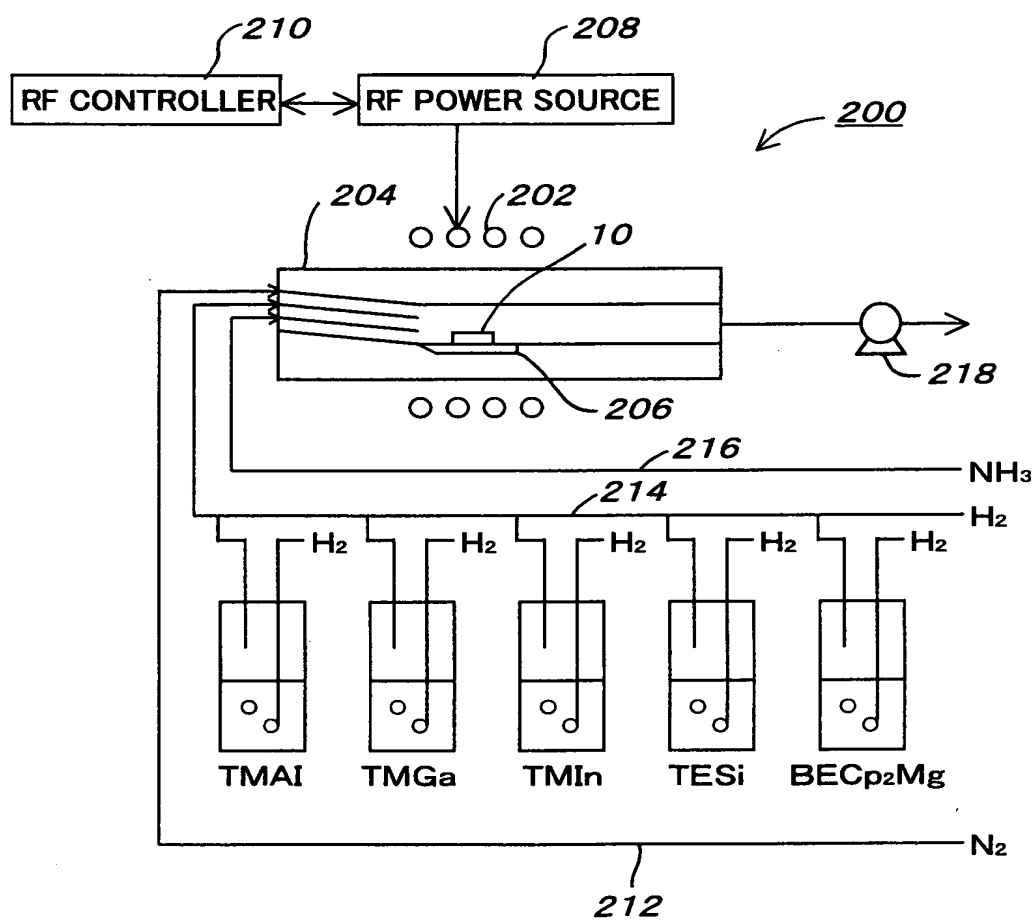


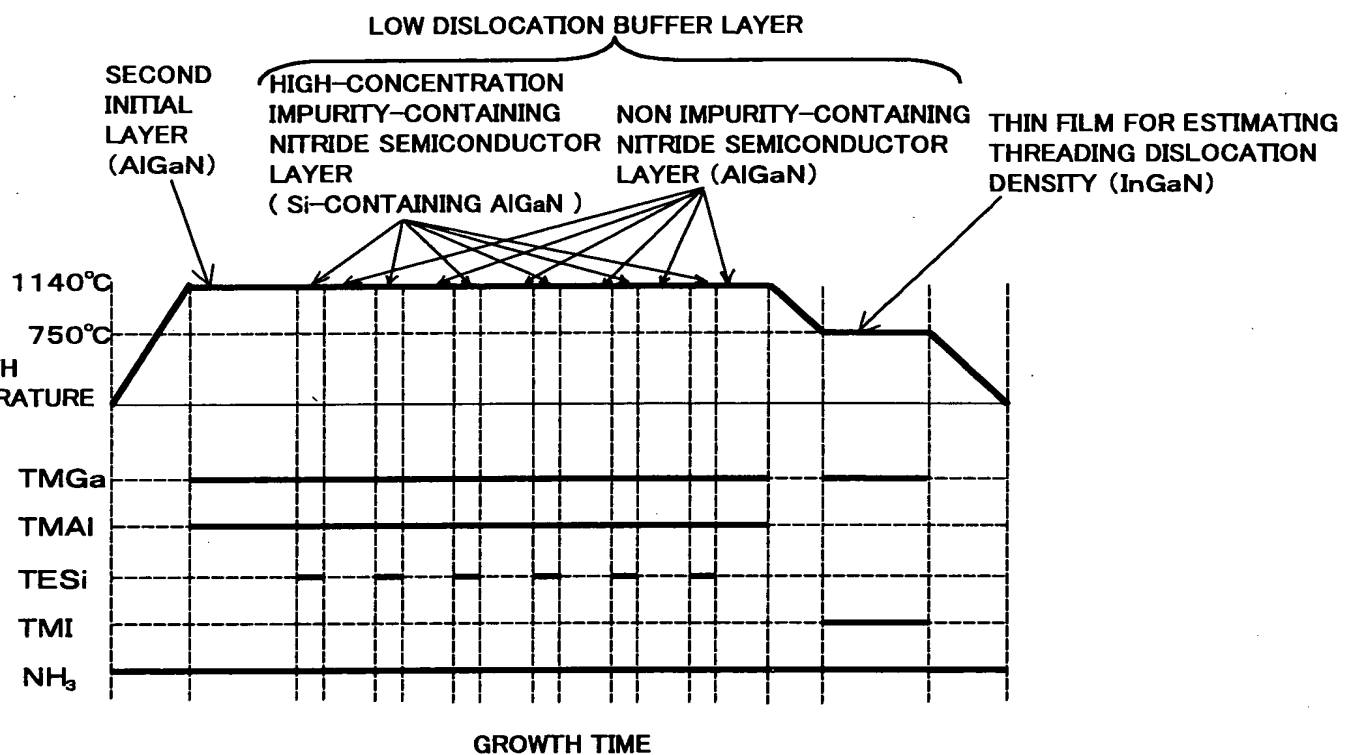
FIG. 5



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FIG. 6

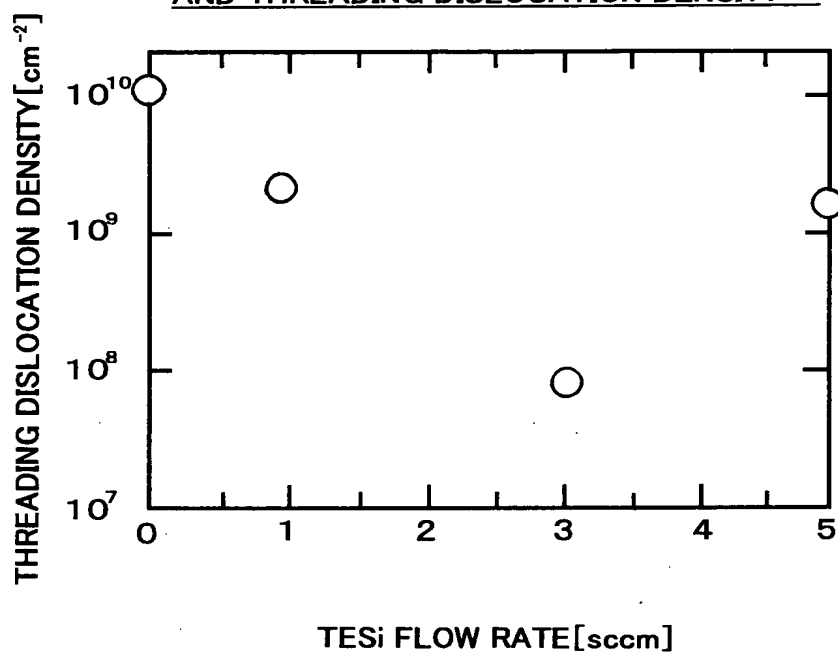
TIMING CHART FOR INTRODUCING MATERIAL GASES



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FIG. 7

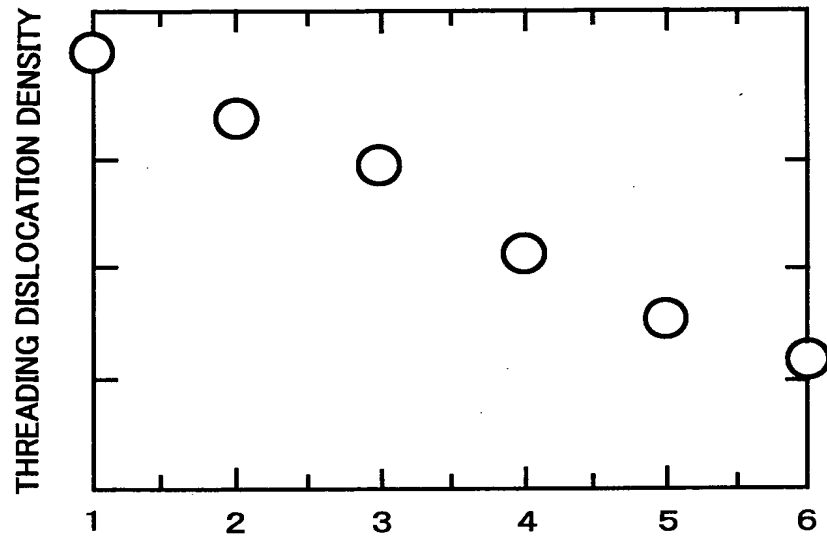
RELATIONSHIP BETWEEN TESi FLOW RATE
AND THREADING DISLOCATION DENSITY



101E30"22E4660

FIG. 8

RELATIONSHIP BETWEEN PERIOD OF
SUPERLATTICE BUFFER LAYER AND
THREADING DISLOCATION DENSITY



PERIODICITY OF SUPERLATTICE BUFFER LAYER (NUMBER OF TIMES)

FIG. 8

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FIG. 9

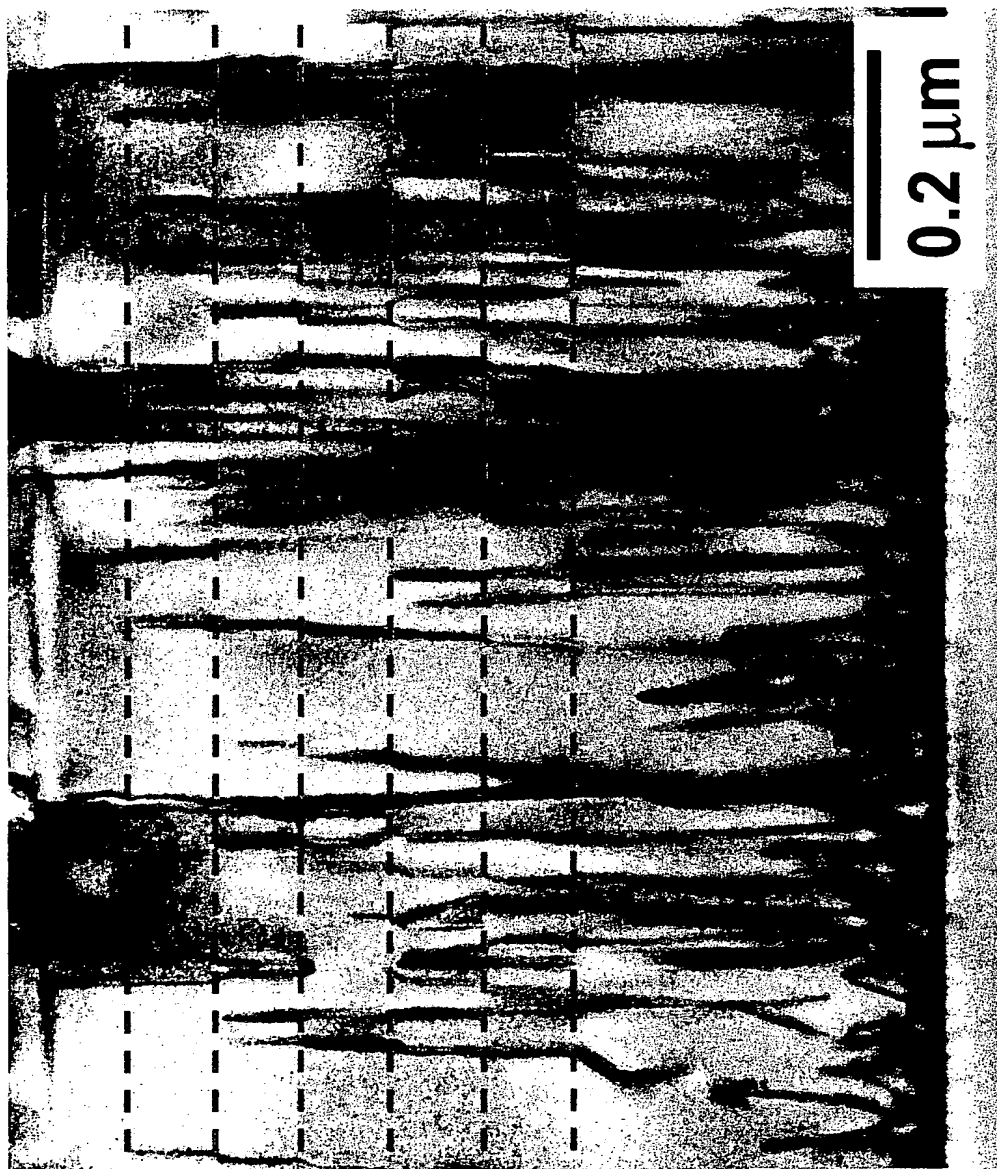


FIG. 10

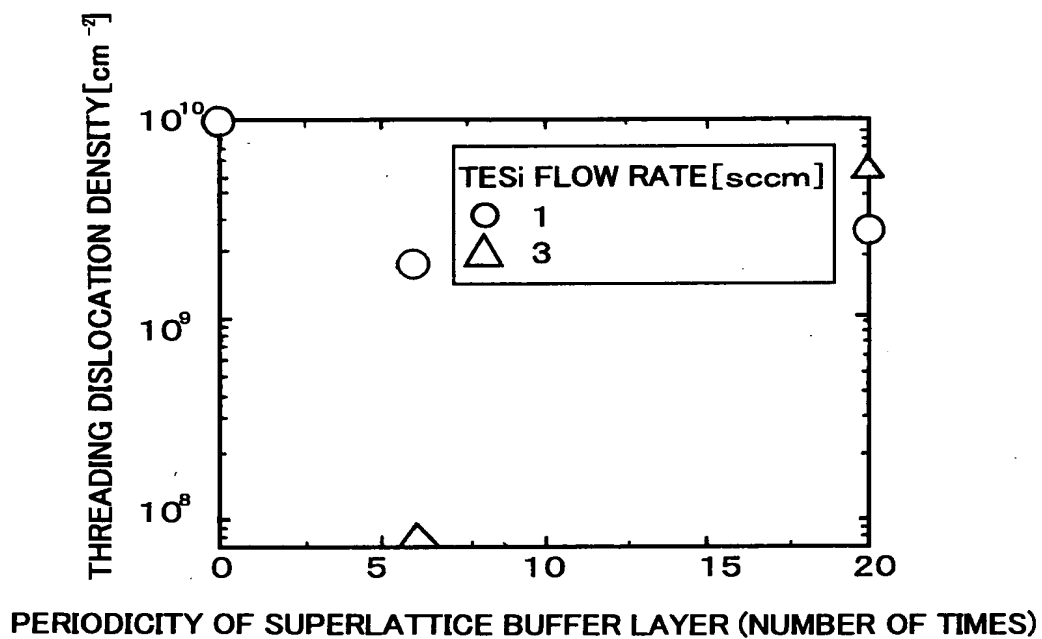
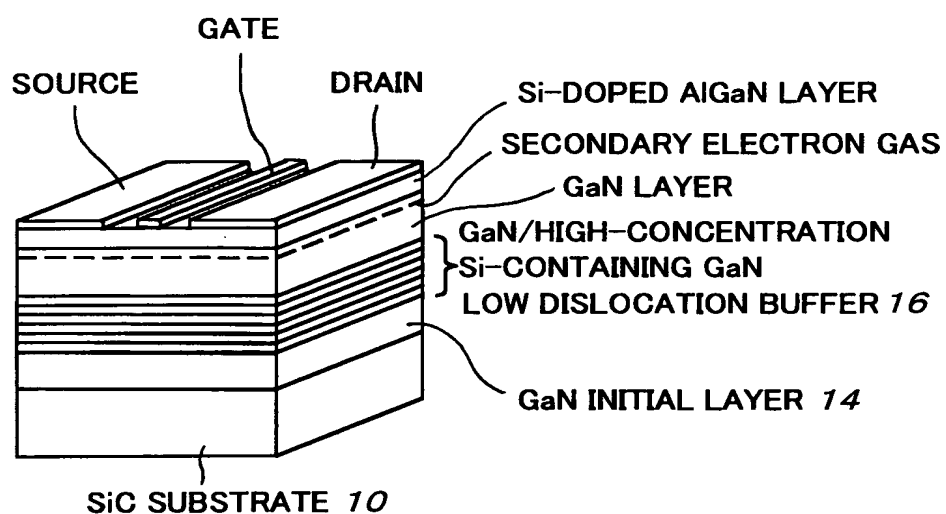


FIG. 11

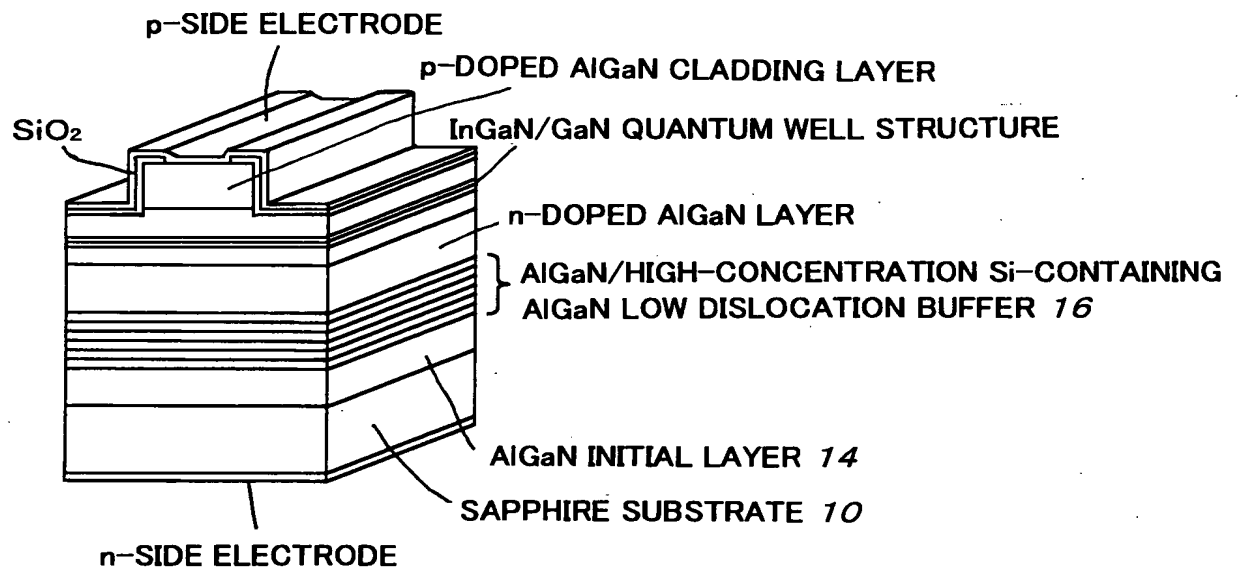
NITRIDE SEMICONDUCTOR HFET
(Heterostructure Field Effect Transistor)
(EXAMPLE, AlGaN/GaN-HFET)



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FIG. 12

NITRIDE SEMICONDUCTOR LASER DIODE
(EXAMPLE, InGaN LASER)



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